

CoolMOS™ Power Transistor

Features

- Worldwide best $R_{DS(on)}$ in TO252
- Ultra low gate charge
- Extreme dv/dt rated
- High peak current capability
- Qualified according to JEDEC¹⁾ for target applications
- Pb-free lead plating; RoHS compliant

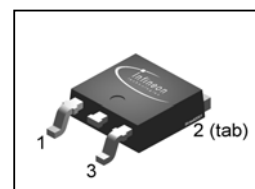
CoolMOS CP is specially designed for:

- Hard switching SMPS topologies

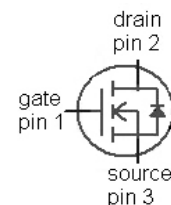
Product Summary

$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	0.385	Ω
$Q_{g,typ}$	17	nC

PG-TO252



Type	Package	Ordering Code	Marking
IPD60R385CP	PG-TO252	SP000062533	6R385P



Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_C=25\text{ °C}$	9.0	A
		$T_C=100\text{ °C}$	5.7	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_C=25\text{ °C}$	27	
Avalanche energy, single pulse	E_{AS}	$I_D=3.4\text{ A}$, $V_{DD}=50\text{ V}$	227	mJ
Avalanche energy, repetitive $t_{AR}^{2),3)}$	E_{AR}	$I_D=3.4\text{ A}$, $V_{DD}=50\text{ V}$	0.3	
Avalanche current, repetitive $t_{AR}^{2),3)}$	I_{AR}		3	A
MOSFET dv/dt ruggedness	dv/dt	$V_{DS}=0\ldots480\text{ V}$	50	V/ns
Gate source voltage	V_{GS}	static	± 20	V
		AC ($f>1\text{ Hz}$)	± 30	
Power dissipation	P_{tot}	$T_C=25\text{ °C}$	83	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 150	°C

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous diode forward current	I_S	$T_C=25\text{ °C}$	5.2	A
Diode pulse current ²⁾	$I_{S,pulse}$		27	
Reverse diode dv/dt ⁴⁾	dv/dt		15	V/ns

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		-	-	1.5	K/W
Thermal resistance, junction - ambient	R_{thJA}	SMD version, device on PCB, minimal footprint	-	-	62	
		SMD version, device on PCB, 6 cm ² cooling area ⁵⁾	-	35	-	
Soldering temperature, reflowsoldering	T_{solder}	reflow MSL3	-	-	260	°C

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}$, $I_D=250\text{ }\mu\text{A}$	600	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=0.34\text{ mA}$	2.5	3	3.5	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=600\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$	-	-	1	μA
		$V_{DS}=600\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=150\text{ °C}$	-	10	-	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}$, $I_D=5.2\text{ A}$, $T_j=25\text{ °C}$	-	0.35	0.385	Ω
		$V_{GS}=10\text{ V}$, $I_D=5.2\text{ A}$, $T_j=150\text{ °C}$	-	0.94	-	
Gate resistance	R_G	$f=1\text{ MHz}$, open drain	-	1.8	-	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=100\text{ V},$ $f=1\text{ MHz}$	-	790	-	pF
Output capacitance	C_{oss}		-	38	-	
Effective output capacitance, energy related ⁶⁾	$C_{o(er)}$	$V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$ to 480 V	-	36	-	
Effective output capacitance, time related ⁷⁾	$C_{o(tr)}$		-	300	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=400\text{ V},$ $V_{GS}=10\text{ V}, I_D=9.9\text{ A},$ $R_G=6.8\ \Omega$	-	10	-	ns
Rise time	t_r		-	5	-	
Turn-off delay time	$t_{d(off)}$		-	40	-	
Fall time	t_f		-	5	-	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD}=400\text{ V}, I_D=5.2\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	4	-	nC
Gate charge at threshold	$Q_{g(th)}$		-	4.6	6.2	
Gate to drain charge	Q_{gd}		-	6	-	
Switching charge	Q_{sw}		-	12	17	
Gate charge total	Q_g		-	17	22	
Gate plateau voltage	$V_{plateau}$		-	5.0	-	V

Reverse Diode

Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=5.2\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	0.9	1.2	V
Reverse recovery time	t_{rr}	$V_R=400\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	260	-	ns
Reverse recovery charge	Q_{rr}		-	3.1	-	μC
Peak reverse recovery current	I_{rrm}		-	24	-	A

¹⁾ J-STD20 and JESD22

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR} \cdot f$.

⁴⁾ $I_{SD}=I_D$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DClamp}=400\text{ V}$, $V_{peak} < V_{(BR)DSS}$, $T_j < T_{j,max}$, identical low side and high side switch

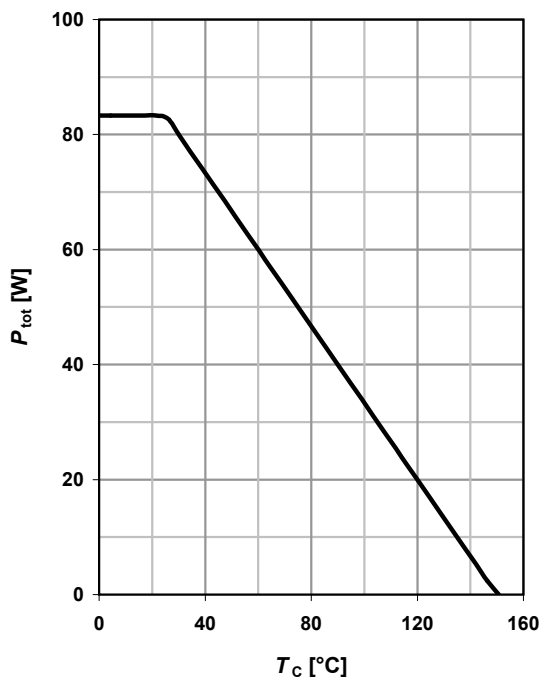
⁵⁾ Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is without blown air.

⁶⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⁷⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

1 Power dissipation

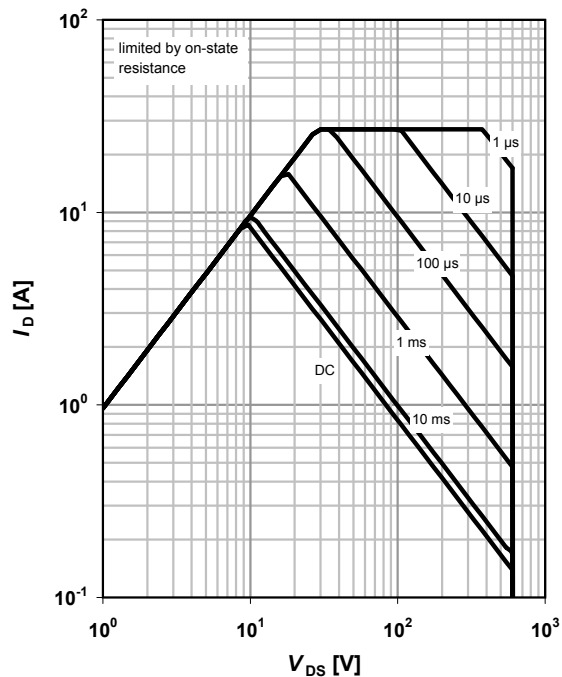
$$P_{\text{tot}} = f(T_C)$$



2 Safe operating area

$$I_D = f(V_{DS}); T_C = 25^\circ\text{C}; D = 0$$

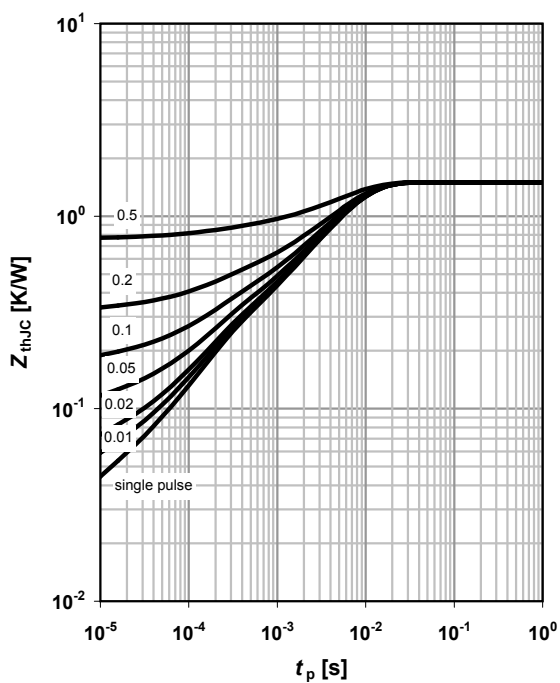
parameter: t_p



3 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

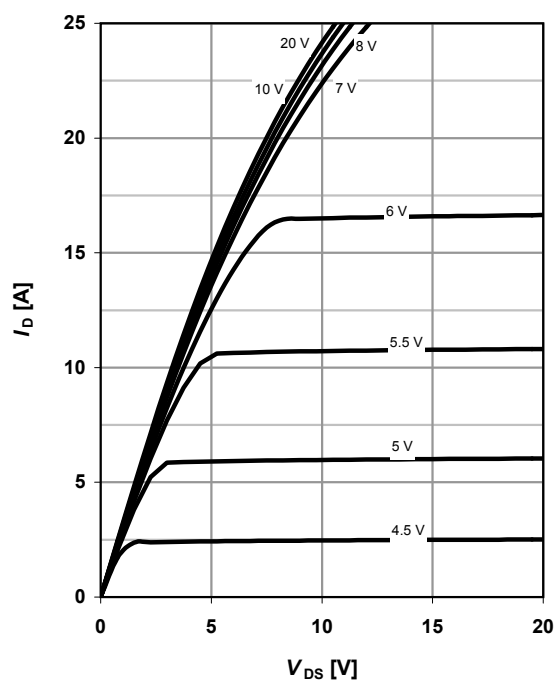
parameter: $D = t_p/T$



4 Typ. output characteristics

$$I_D = f(V_{DS}); T_J = 25^\circ\text{C}$$

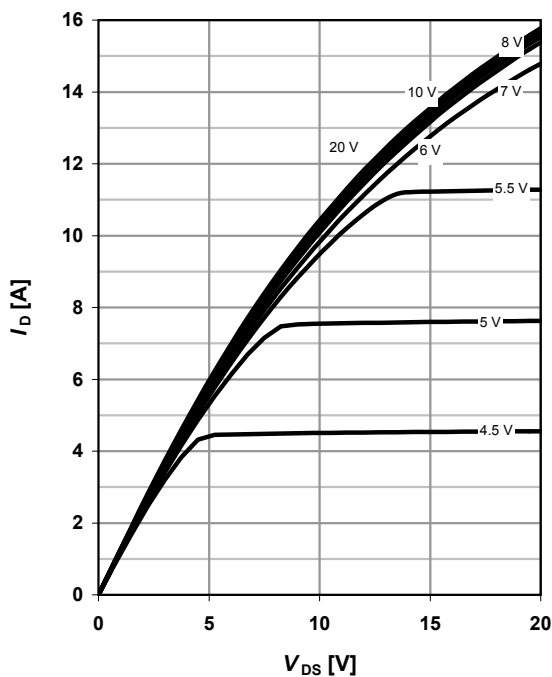
parameter: V_{GS}



5 Typ. output characteristics

$$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$$

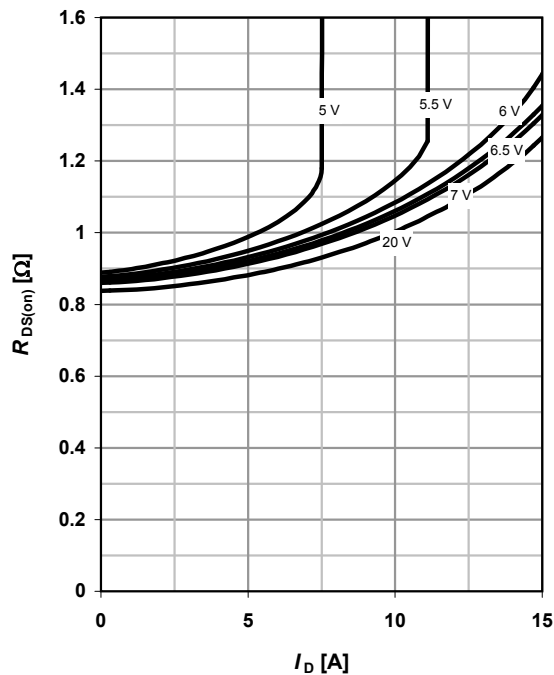
parameter: V_{GS}



6 Typ. drain-source on-state resistance

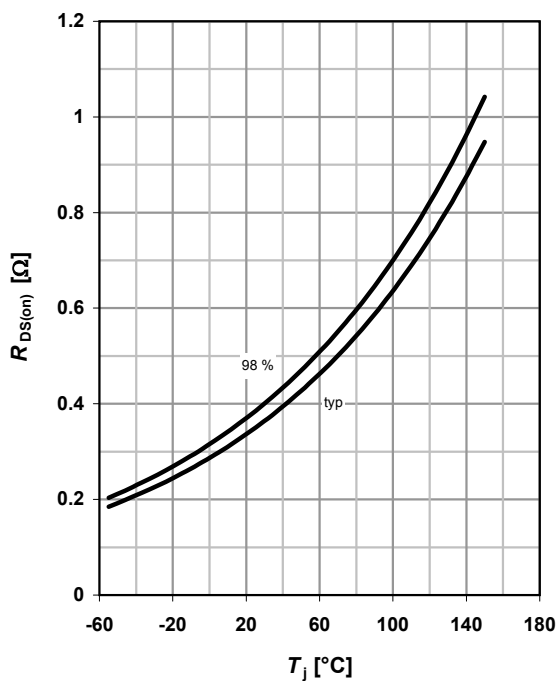
$$R_{DS(on)} = f(I_D); T_j = 150^\circ\text{C}$$

parameter: V_{GS}



7 Drain-source on-state resistance

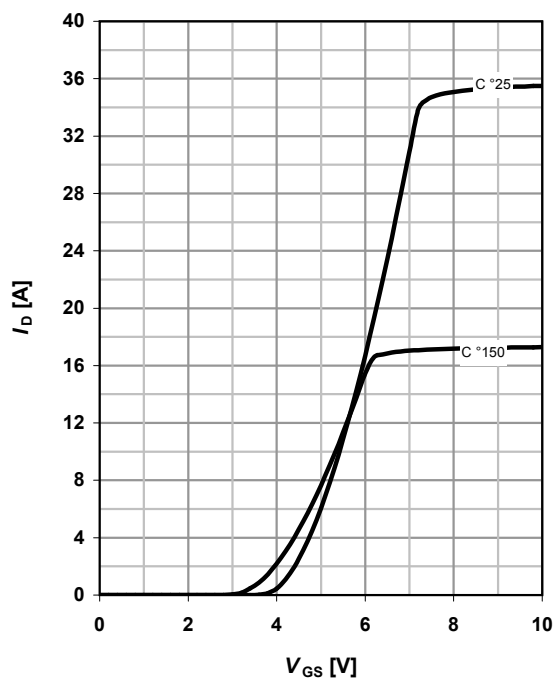
$$R_{DS(on)} = f(T_j); I_D = 5.2\text{ A}; V_{GS} = 10\text{ V}$$



8 Typ. transfer characteristics

$$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|/R_{DS(on)\max}$$

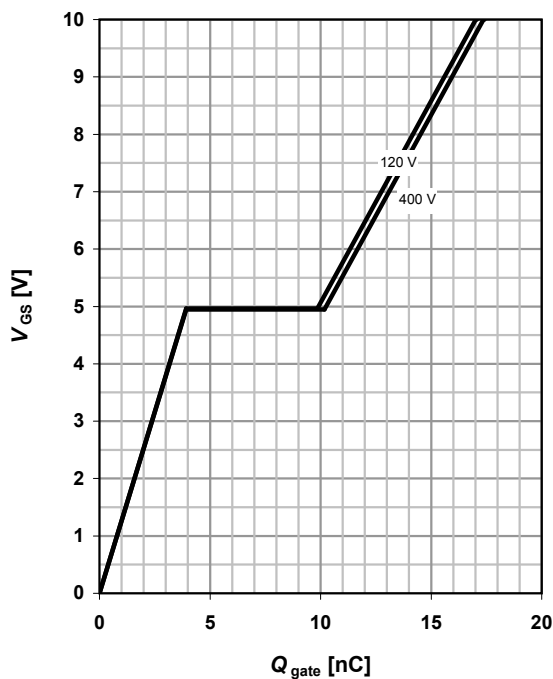
parameter: T_j



9 Typ. gate charge

$$V_{GS}=f(Q_{gate}); I_D=5.2 \text{ A pulsed}$$

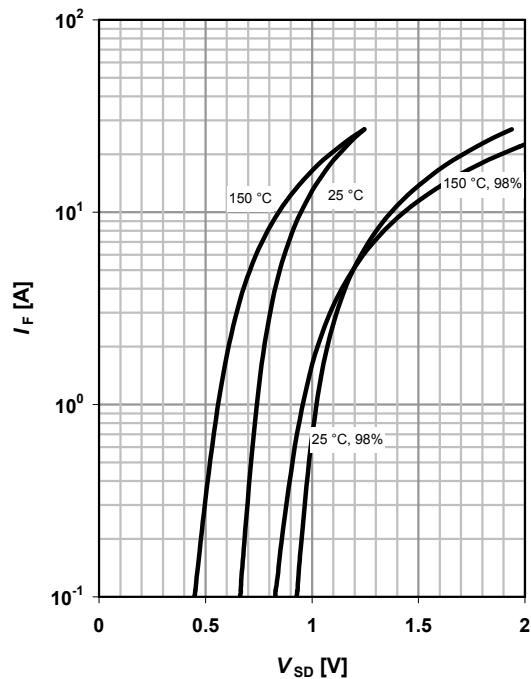
parameter: V_{DD}



10 Forward characteristics of reverse diode

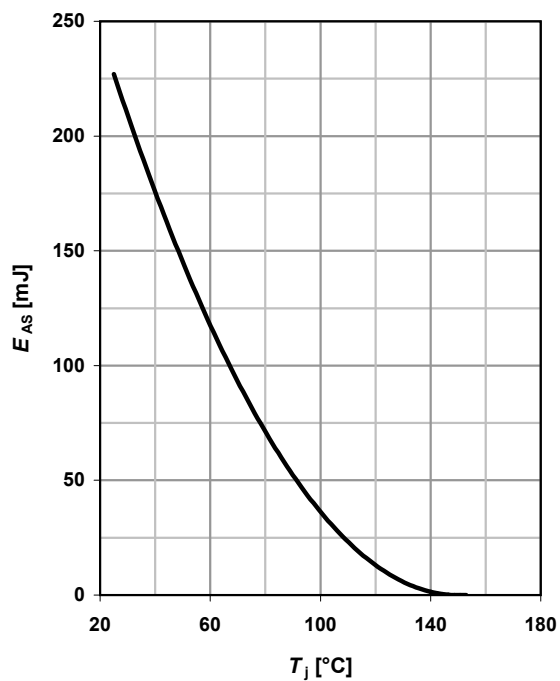
$$I_F=f(V_{SD})$$

parameter: T_j



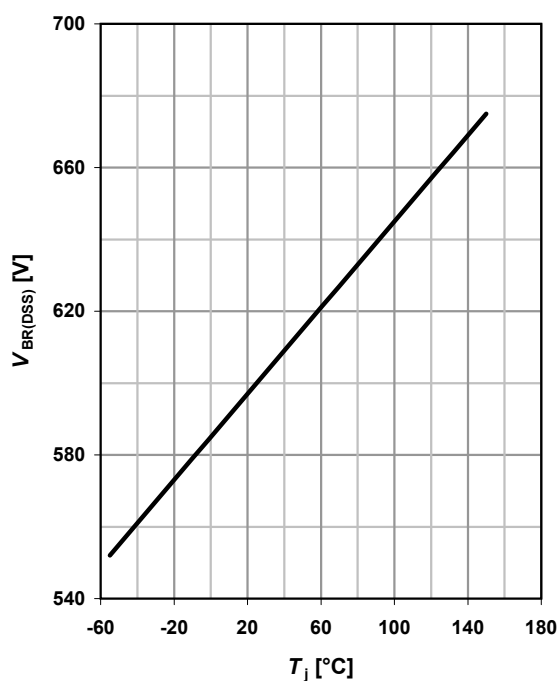
11 Avalanche energy

$$E_{AS}=f(T_j); I_D=3.4 \text{ A}; V_{DD}=50 \text{ V}$$

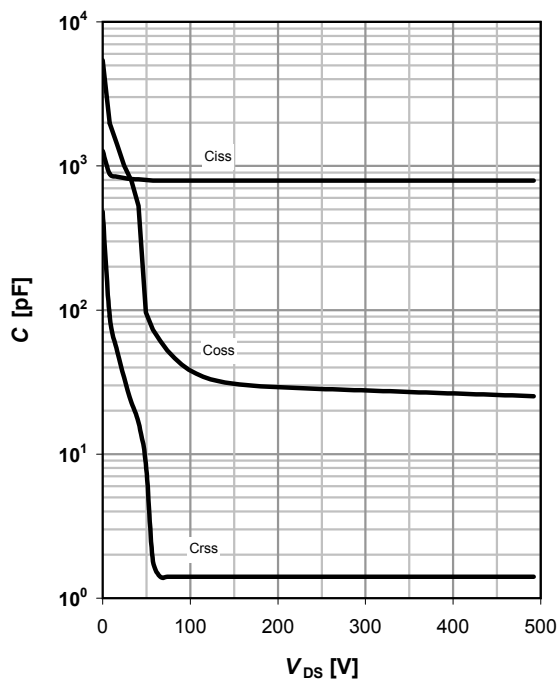


12 Drain-source breakdown voltage

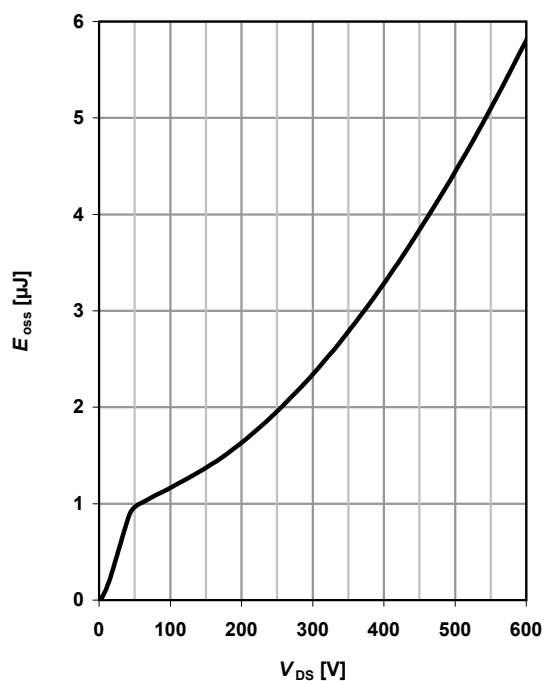
$$V_{BR(DSS)}=f(T_j); I_D=0.25 \text{ mA}$$



13 Typ. capacitances

 $C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$


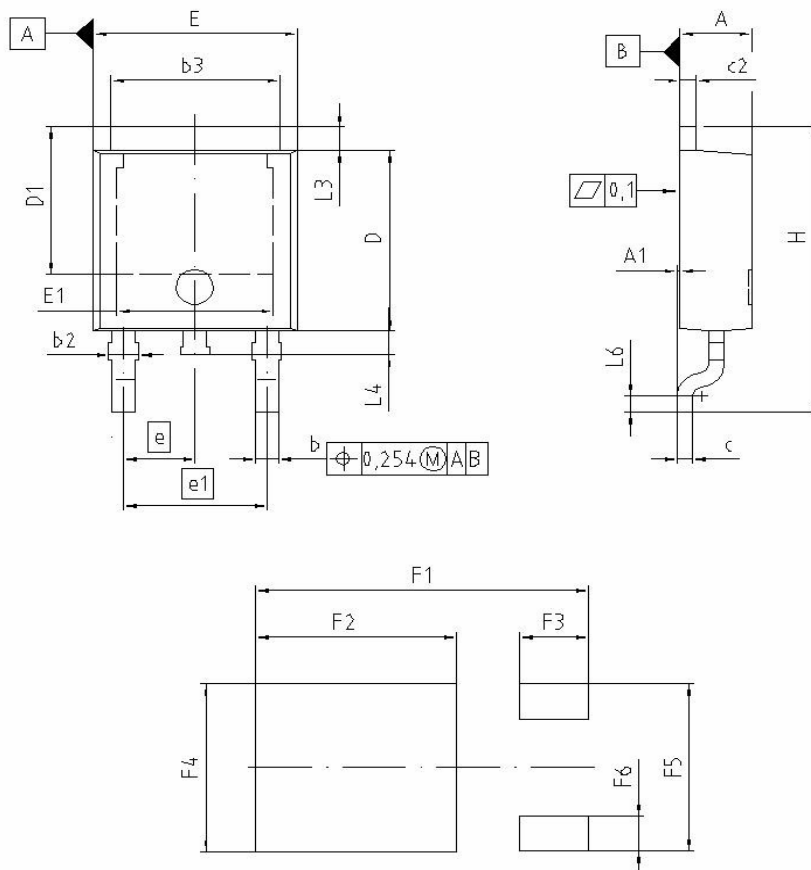
14 Typ. Coss stored energy

 $E_{oss} = f(V_{DS})$


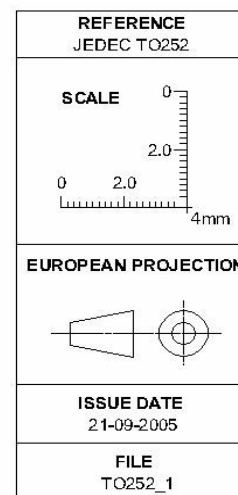
Definition of diode switching characteristics



PG-T0252-3-1/T0252-3-11/T0252-3-21: Outlines



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.159	2.413	0.085	0.095
A1	0.000	0.150	0.000	0.006
b	0.635	0.889	0.025	0.035
b2	0.650	1.150	0.026	0.045
b3	5.004	5.500	0.197	0.217
c	0.457	0.580	0.018	0.023
c2	0.460	0.980	0.018	0.039
D	5.969	6.223	0.235	0.245
D1	5.020	5.842	0.198	0.230
E	6.400	6.731	0.252	0.265
E1	4.850	5.207	0.191	0.205
e	2.286		0.090	
e1	4.572		0.180	
N	3		3	
H	9.400	10.480	0.370	0.413
L3	0.900	1.143	0.035	0.045
L4	0.584	0.950	0.023	0.037
L6	0.510	0.686	0.020	0.027
F1	10.500	10.700	0.413	0.421
F2	6.300	6.500	0.248	0.256
F3	2.100	2.300	0.083	0.091
F4	5.700	5.900	0.224	0.232
F5	5.860	5.860	0.222	0.231
F6	1.100	1.300	0.043	0.051



Dimensions in mm/inches:

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